

NCE N-Channel Super Trench Power MOSFET

Description

The NCEP6090K uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

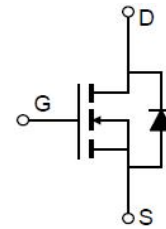
General Features

- $V_{DS} = 60V, I_D = 90A$
 $R_{DS(ON)} < 6.9m\Omega @ V_{GS} = 10V$ (Typ: 6.4m Ω)
- Excellent gate charge x $R_{DS(on)}$ product
- Very low on-resistance $R_{DS(on)}$
- Pb-free lead plating
- 100% UIS tested

Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

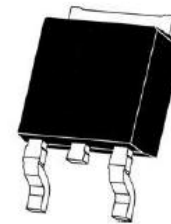
100% UIS TESTED!
100% ΔV_d s TESTED!



Schematic diagram



Marking and pin assignment



TO-252 -2Ltop view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP6090K	NCEP6090K	TO-252-2L	Ø330mm	12mm	2500Pcs

Absolute Maximum Ratings ($T_c = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous (Silicon Limited)	I_D	90	A
Drain Current-Continuous ($T_c = 100^\circ C$)	$I_D(100^\circ C)$	63.6	A
Pulsed Drain Current	I_{DM}	360	A
Maximum Power Dissipation	P_D	100	W
Derating factor		0.67	W/ $^\circ C$
Single pulse avalanche energy ^(Note 5)	E_{AS}	320	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 175	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	$R_{\theta JC}$	1.50	$^\circ C/W$
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Electrical Characteristics (T_c=25°C unless otherwise noted)

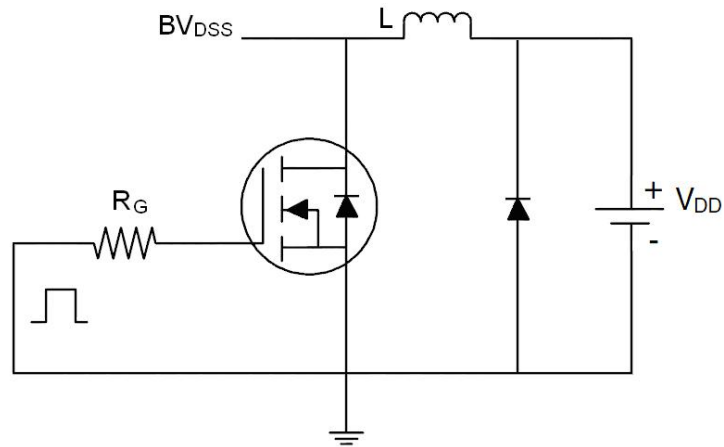
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	60		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	2	3	4	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =45A	-	6.4	6.9	mΩ
Gate resistance	R _G	V _{DS} =0V, V _{GS} =0V, F=1.0MHz	-	3	-	Ω
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =45A	-	35	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{iss}	V _{DS} =30V, V _{GS} =0V, F=1.0MHz	-	1700	-	PF
Output Capacitance	C _{oss}		-	345	-	PF
Reverse Transfer Capacitance	C _{rss}		-	8	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =30V, I _D =45A V _{GS} =10V, R _G =4.7Ω	-	8	-	nS
Turn-on Rise Time	t _r		-	2	-	nS
Turn-Off Delay Time	t _{d(off)}		-	29	-	nS
Turn-Off Fall Time	t _f		-	4	-	nS
Total Gate Charge	Q _g	V _{DS} =30V, I _D =45A, V _{GS} =10V	-	26.9		nC
Gate-Source Charge	Q _{gs}		-	9.4		nC
Gate-Drain Charge	Q _{gd}		-	4.6		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =45A	-		1.2	V
Diode Forward Current (Note 2)	I _S		-	-	90	A
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = I _S di/dt = 100A/μs (Note3)	-	38		nS
Reverse Recovery Charge	Q _{rr}		-	48		nC

Notes:

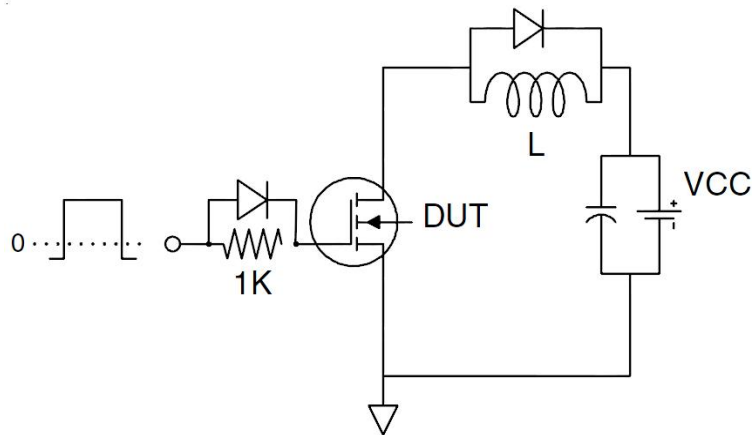
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production
5. EAS condition : T_j=25°C, V_{DD}=30V, V_G=10V, L=0.5mH, R_G=25Ω

Test Circuit

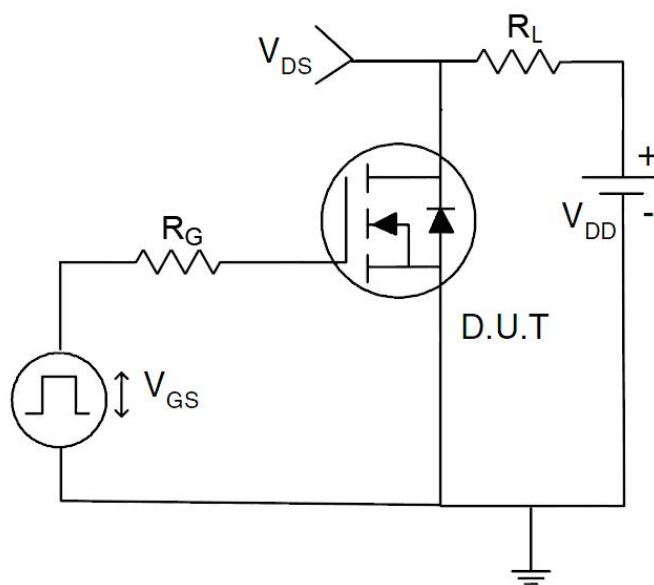
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics

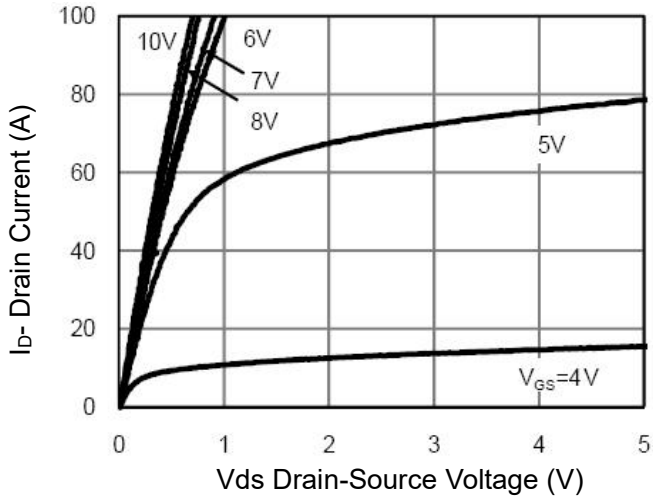


Figure 1 Output Characteristics

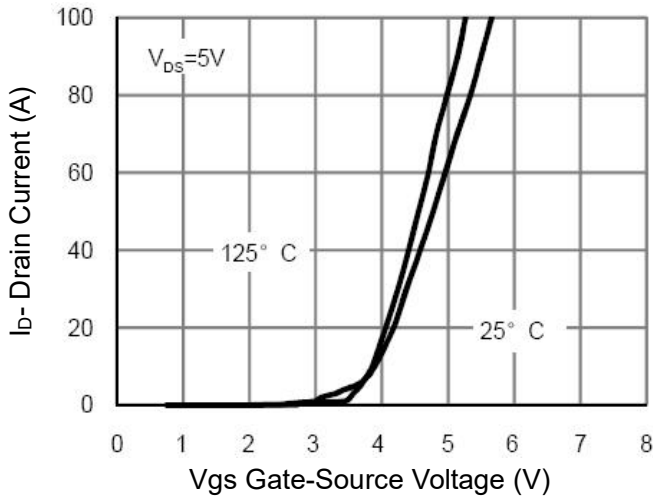


Figure 2 Transfer Characteristics

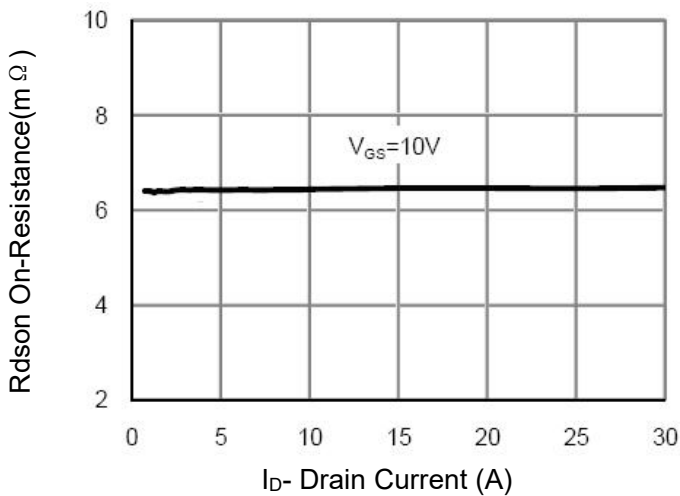


Figure 3 Rds(on)- Drain Current

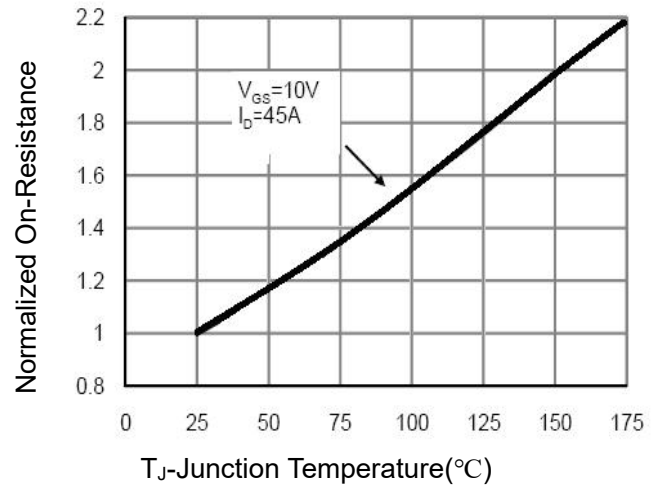


Figure 4 Rds(on)-Junction Temperature

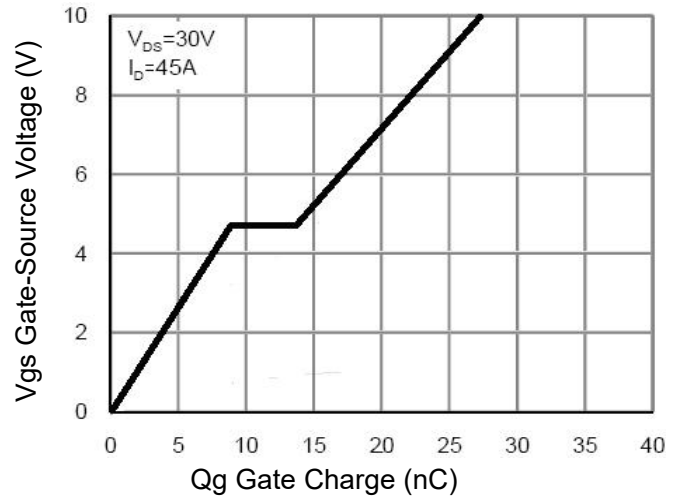


Figure 5 Gate Charge

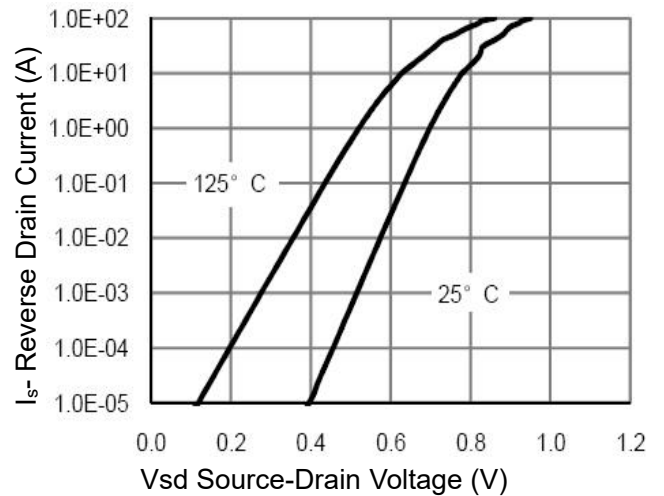


Figure 6 Source- Drain Diode Forward

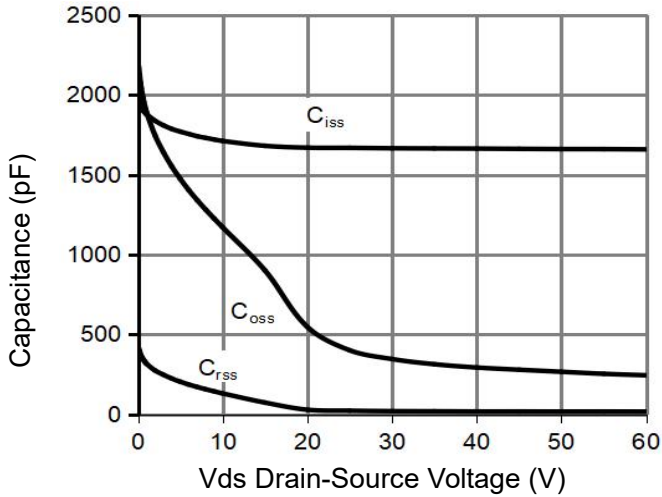


Figure 7 Capacitance vs Vds

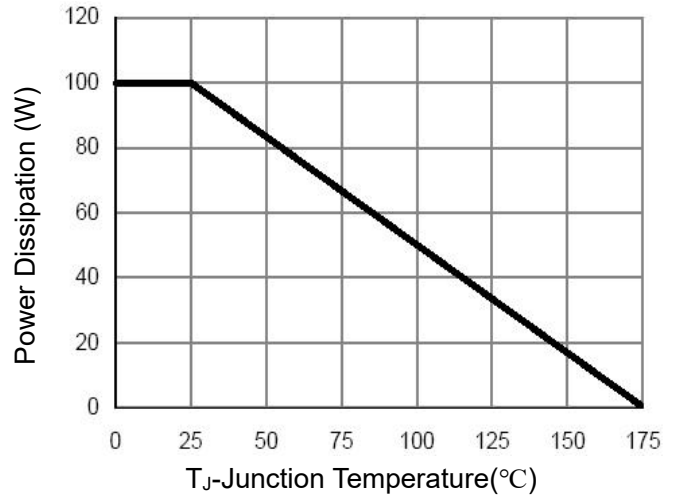


Figure 9 Power De-rating

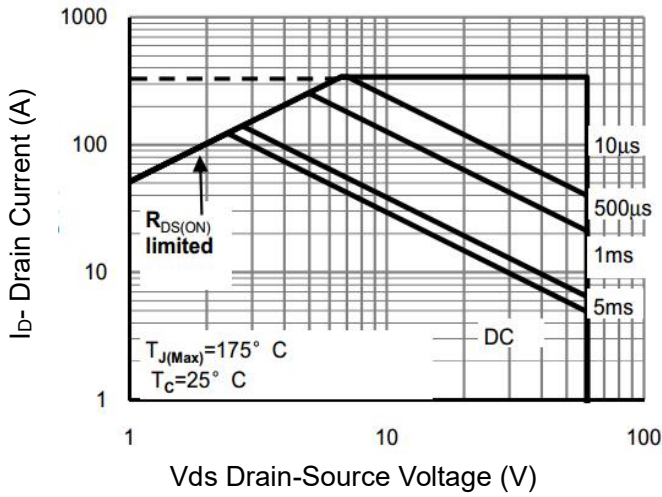


Figure 8 Safe Operation Area

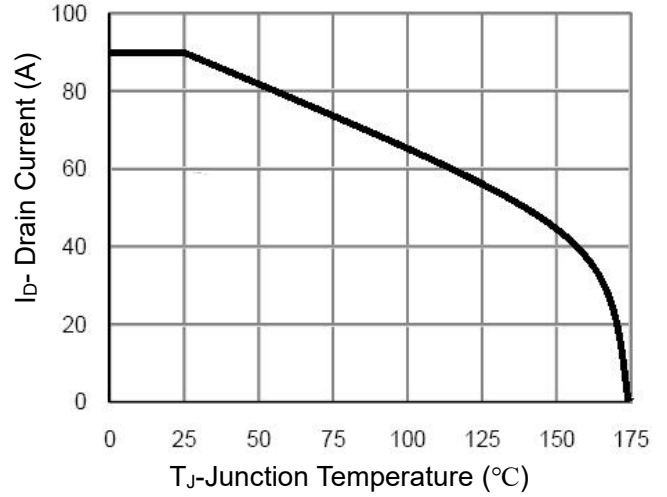


Figure 10 Current De-rating

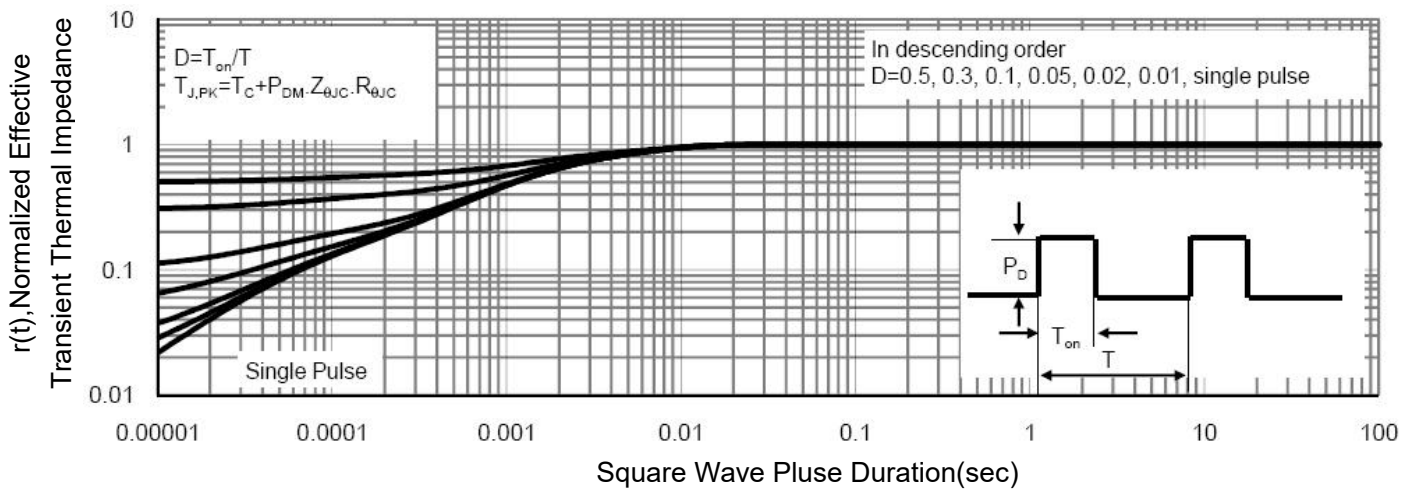
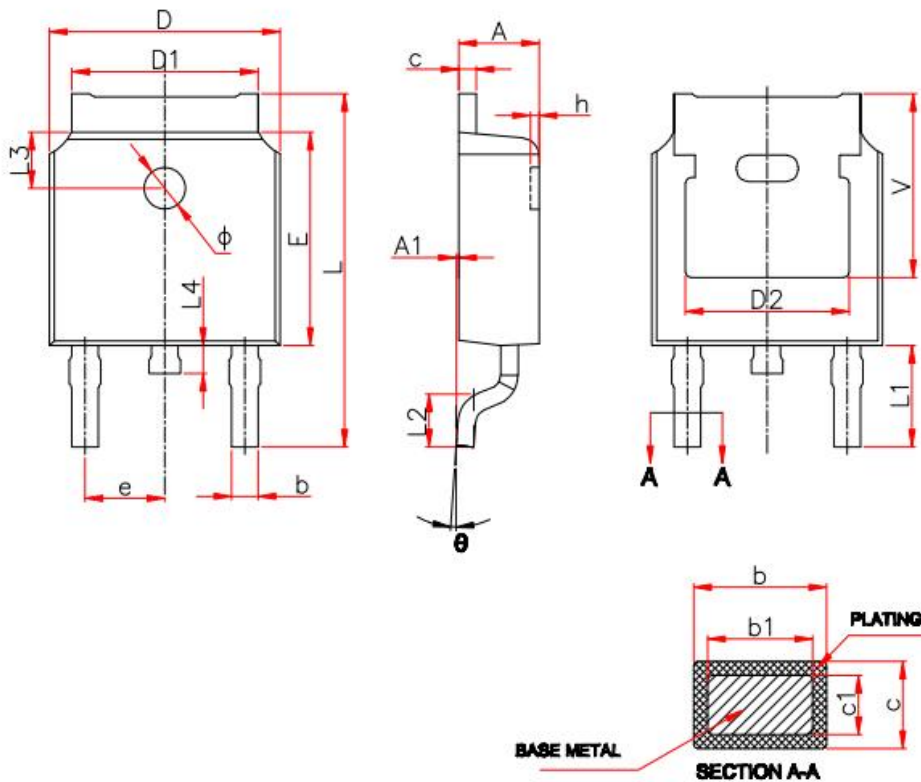


Figure 11 Normalized Maximum Transient Thermal Impedance

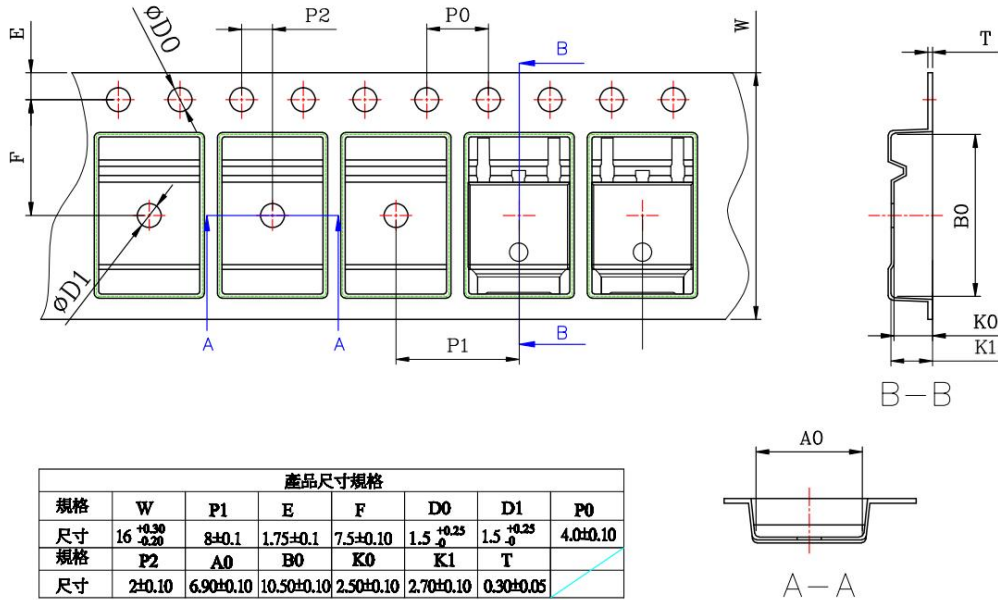
TO-252 Package Information



Symbol	Millimeters	
	Min.	Max.
A	2.20	2.40
A1	0.00	0.13
b	0.66	0.86
b1	0.73	0.79
c	0.46	0.58
c1	0.50	0.52
D	6.50	6.70
D1	5.10	5.46
D2	4.83 REF.	
E	6.00	6.20
e	2.19	2.39
L	9.80	10.40
L1	2.90 REF.	
L2	1.40	1.70
L3	1.60 REF.	
L4	0.60	1.00
Φ	1.10	1.30
θ	0°	8°

包装信息

一、载带图纸:



二、包装信息表 (满箱信息)

封装形式	包装方式	盘尺寸	只/盘	盘/内盒	只/内盒	内盒/箱	只/箱
TO-252	编带	13 寸	2500	1	2500	8	20000

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